



2SC2275

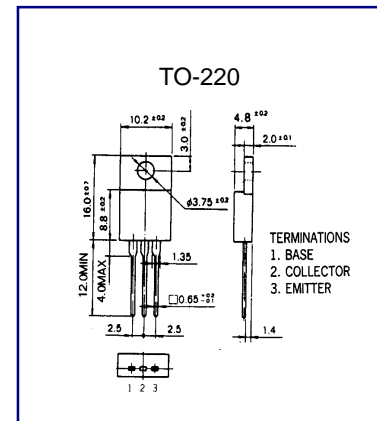
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SA985

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

| Characteristic | Symbol | Rating | Unit |
|--|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | 120 | V |
| Collector-Emitter Voltage | V _{CE0} | 120 | V |
| Emitter-Base voltage | V _{EB0} | 7 | V |
| Collector Current (DC) | I _C | 1.5 | A |
| Collector Dissipation ($T_c=25^\circ\text{C}$) | P _C | 25 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature | T _{stg} | -50~150 | °C |



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------------------|----------------------|---|-----|-----|-----|------|
| Collector Cutoff Current | I _{CBO} | V _{CB} = 120V , I _E =0 | | | 100 | μA |
| Emitter Cutoff Current | I _{EB0} | V _{EB} = 7V , I _C =0 | | | 100 | μA |
| DC Current Gain | h _{FE1} | V _{CE} = 5V , I _C =0.3A | | 150 | | |
| Collector- Emitter Saturation Voltage | V _{CE(sat)} | I _C =2A , I _B =0.2A | | | 1.5 | V |
| Current Gain Bandwidth Product | f _T | V _{CE} = 5V , I _C =0.5A | | 180 | | MHZ |

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.